



2N7002AQ

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
60V	$6\Omega @ V_{GS} = 5V$	200mA

#### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The 2N7002AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

### **Description and Applications**

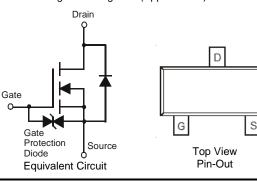
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)





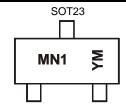
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
2N7002AQ-7	SOT23	3,000/Tape & Reel
2N7002AQ-13	SOT23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



 $\begin{array}{l} MN1 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ H=2020) \\ M = Month\ (ex:\ 9 = September) \end{array}$ 

#### Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н		J	K	L	M	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	60	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	l <sub>D</sub>	180 130 115	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	l <sub>D</sub>	220 160 140	mA		
Maximum Continuous Body Diode Forward Current	(Note 6)	Is	220	mA	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	)		I <sub>DM</sub>	800	mA

# Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D	370	mW	
Total Power Dissipation	(Note 6)	P <sub>D</sub>	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	ב	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	91		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

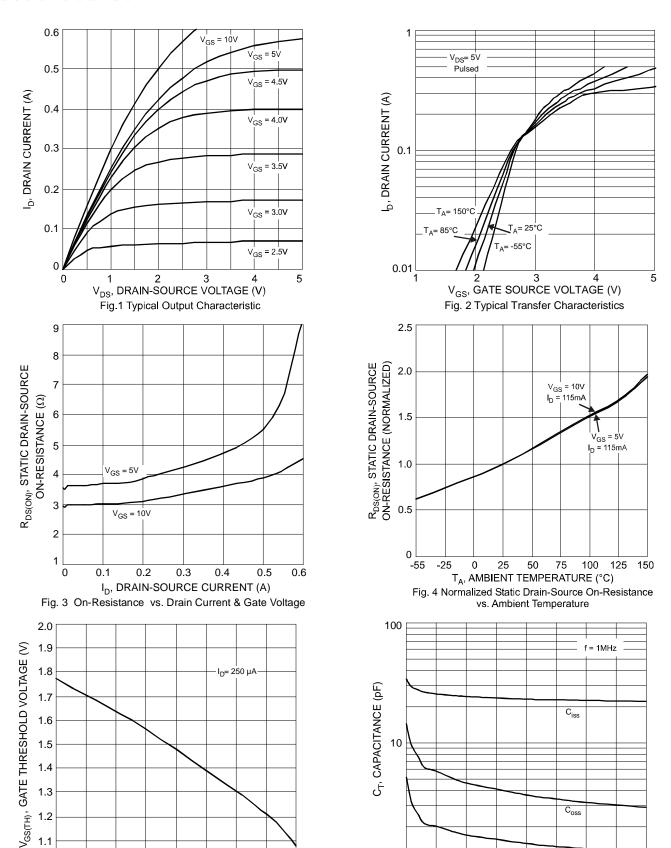
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							•
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	60	70	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$		I <sub>DSS</sub>	_	_	1.0 500	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage		I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V <sub>GS(th)</sub>	1.2	_	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance @ T <sub>J</sub> = +25°C		<b>D</b>		3.5	6	Ω	$V_{GS} = 5.0V, I_D = 0.115A$
	@ T <sub>J</sub> = +125°C	R <sub>DS(ON)</sub>	_	3.0	5	12	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A
Forward Transconductance		<b>g</b> FS	80	_	_	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A
DYNAMIC CHARACTERISTICS (Note	8)			•			
Input Capacitance		C <sub>iss</sub>	_	23	_	pF	
Output Capacitance		Coss	_	3.4	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	Reverse Transfer Capacitance		_	1.4	_	pF	
Gate Resistance		$R_{G}$	_	260	400	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (No	ote 8)			•			
Turn-On Delay Time		t <sub>D(ON)</sub>	_	10	_	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.115A, R <sub>L</sub> = 150
Turn-Off Delay Time			_	33	_	ns	$\Omega$ , V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25 $\Omega$

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





-25

25

75

50

 $T_A$ , AMBIENT TEMPERATURE ( °C )

Fig. 5 Gate Threshold Variation vs. Ambient Temperature

100

125 150

1.0

-50

1

0

 $C_{rss}$ 

25

15

20

 $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V)

Fig. 6 Typical Total Capacitance

30

35



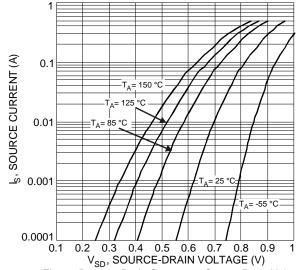
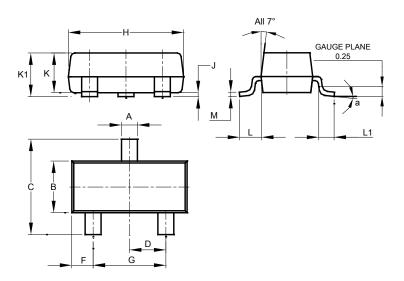


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

## **Package Outline Dimensions**

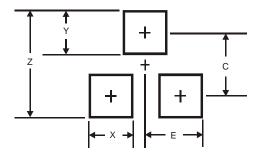
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	1.78 2.05						
Η	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
٦	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	a 8°							
All	All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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